

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3325

AUDIO FREQUENCY LOW POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

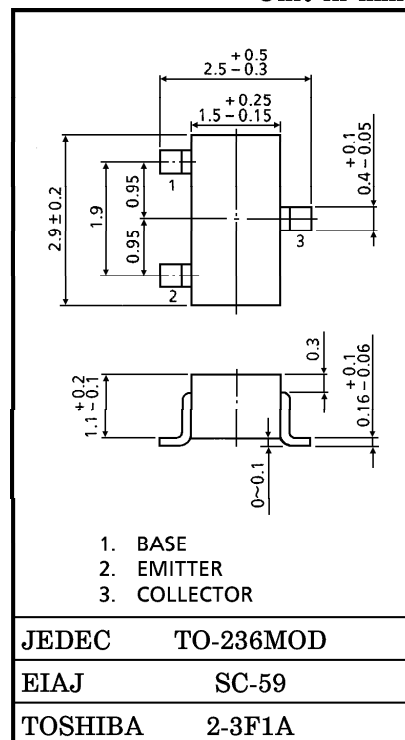
SWITCHING APPLICATIONS

Unit in mm

- Excellent h_{FE} Linearity : $h_{FE} (2) = 25$ (Min.)
($V_{CE} = 6\text{ V}$, $I_C = 400\text{ mA}$)
- High Voltage : $V_{CEO} = 50\text{ V}$ (Min.)
- Complementary to 2SA1313
- Small Package

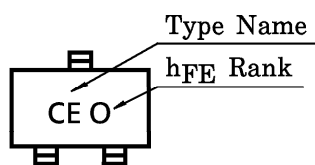
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight : 0.012 g

MARKING



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	70	—	240	
	$h_{FE(2)}$ (Note)	$V_{CE} = 6\text{ V}, I_C = 400\text{ mA}$	25	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$	—	0.1	0.25	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	—	0.8	1.0	V
Transition Frequency	f_T	$V_{CE} = 6\text{ V}, I_C = 20\text{ mA}$	—	300	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 6\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	7	—	pF

(Note) : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240
 $h_{FE(2)}$ Classification O : 25 (Min.), Y : 40 (Min.)

